

Supplementary Material: Hole Injection

Enhancement of MoO₃/NPB/Al Composite Anode

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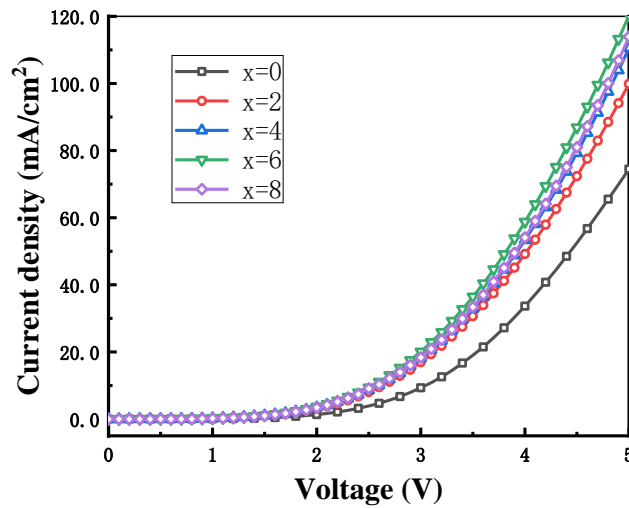


Fig. S1. Current–voltage characteristics of devices with structure ITO/NPB (100 nm)/MoO₃ (5 nm)/CuPc (x nm)/Al.

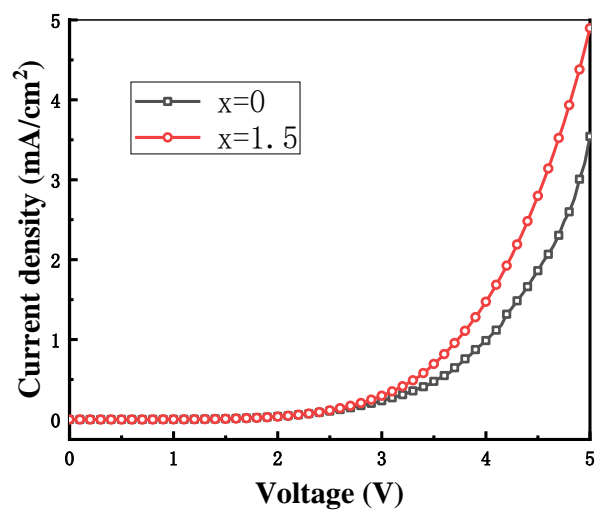


Fig. S2. Current–voltage characteristics of devices with structure ITO/TAPC (100 nm)/MoO₃ (5 nm)/NPB (x nm)/Al.

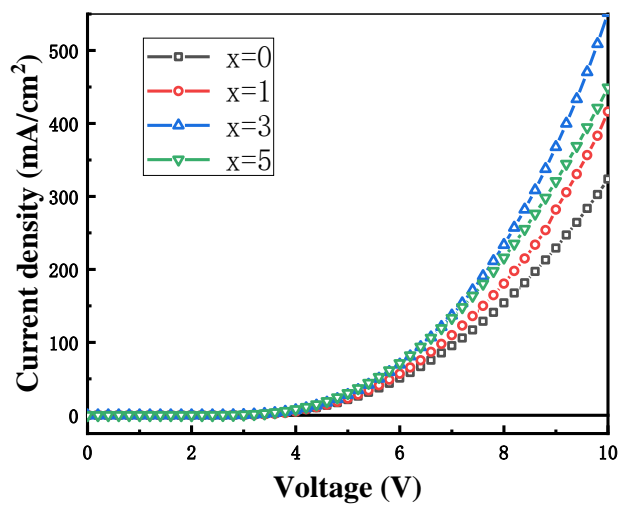


Fig. S3. Current–voltage characteristics of devices with structure ITO/NPB (x nm)/MoO₃ (5 nm)/NPB (100 nm)/Al.